

CoolMOS® Power Transistor

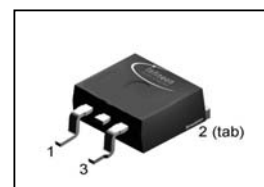
Features

- new revolutionary high voltage technology
- Extreme dv/dt rated
- High peak current capability
- Qualified according to JEDEC¹⁾ for target applications
- Pb-free lead plating; RoHS compliant
- Ultra low gate charge
- Ultra low effective capacitances

Product Summary

V_{DS}	800	V
$R_{DS(on)max} @ T_j = 25^{\circ}C$	0.29	Ω
$Q_{g,typ}$	91	nC

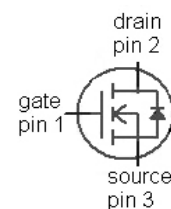
PG-TO263



CoolMOS C3 designed for:

- Industrial application with high DC bulk voltage
- Switching Application (Active Clamp Forward Topology)

Type	Package	Marking
SPB17N80C3	PG-TO263	17N80C3



Maximum ratings, at $T_j=25^{\circ}C$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$T_C=25^{\circ}C$	17	A
		$T_C=100^{\circ}C$	11	
Pulsed drain current ²⁾	$I_{D,pulse}$	$T_C=25^{\circ}C$	51	
Avalanche energy, single pulse	E_{AS}	$I_D=3.4 A, V_{DD}=50 V$	670	mJ
Avalanche energy, repetitive $t_{AR}^{2),3)}$	E_{AR}	$I_D=17 A, V_{DD}=50 V$	0.5	
Avalanche current, repetitive $t_{AR}^{2),3)}$	I_{AR}		17	A
MOSFET dv/dt ruggedness	dv/dt	$V_{DS}=0...640 V$	50	V/ns
Gate source voltage	V_{GS}	static	± 20	V
		AC ($f>1 Hz$)	± 30	
Power dissipation	P_{tot}	$T_C=25^{\circ}C$	227	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 150	$^{\circ}C$

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous diode forward current	I_S	$T_C=25\text{ °C}$	17	A
Diode pulse current ²⁾	$I_{S,pulse}$		51	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		-	-	0.55	K/W
Thermal resistance, junction - ambient	R_{thJA}	SMD version, device on PCB, minimal footprint	-	-	62	
		SMD version, device on PCB, 6 cm ² cooling area ⁴⁾	-	35	-	
Soldering temperature, reflow soldering, MSL1	T_{solder}	1.6 mm (0.063 in.) from case for 10 s	-	-	260	°C

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}$, $I_D=250\text{ }\mu\text{A}$	800	-	-	V
Avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS}=0\text{ V}$, $I_D=17\text{ A}$	-	870	-	
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=1.0\text{ mA}$	2.1	3	3.9	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=800\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$	-	-	25	μA
		$V_{DS}=800\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=150\text{ °C}$	-	150	-	
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}$, $I_D=11\text{ A}$, $T_j=25\text{ °C}$	-	0.25	0.29	Ω
		$V_{GS}=10\text{ V}$, $I_D=11\text{ A}$, $T_j=150\text{ °C}$	-	0.67	-	
Gate resistance	R_G	$f=1\text{ MHz}$, open drain	-	0.85	-	Ω

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=100\text{ V},$ $f=1\text{ MHz}$	-	2300	-	pF
Output capacitance	C_{oss}		-	100	-	
Effective output capacitance, energy related ⁵⁾	$C_{o(er)}$	$V_{GS}=0\text{ V}, V_{DS}=0\text{ V}$ to 480 V	-	72	-	
Effective output capacitance, time related ⁶⁾	$C_{o(tr)}$		-	210	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=400\text{ V},$ $V_{GS}=0/10\text{ V}, I_D=17\text{ A},$ $R_G=4.7\text{ }\Omega,$ $T_j = 125^\circ\text{C}$	-	45	-	ns
Rise time	t_r		-	18	-	
Turn-off delay time	$t_{d(off)}$		-	85	-	
Fall time	t_f		-	15	-	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD}=640\text{ V}, I_D=17\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	12	-	nC
Gate to drain charge	Q_{gd}		-	48	-	
Gate charge total	Q_g		-	91	177	
Gate plateau voltage	$V_{plateau}$		-	5.5	-	V

Reverse Diode

Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=I_S,$ $T_j=25^\circ\text{C}$	-	1	1.2	V
Reverse recovery time	t_{rr}	$V_R=400\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	550	-	ns
Reverse recovery charge	Q_{rr}		-	15	-	μC
Peak reverse recovery current	I_{rrm}		-	51	-	A

¹⁾ J-STD20 and JESD22

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Repetitive avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR} \cdot f$.

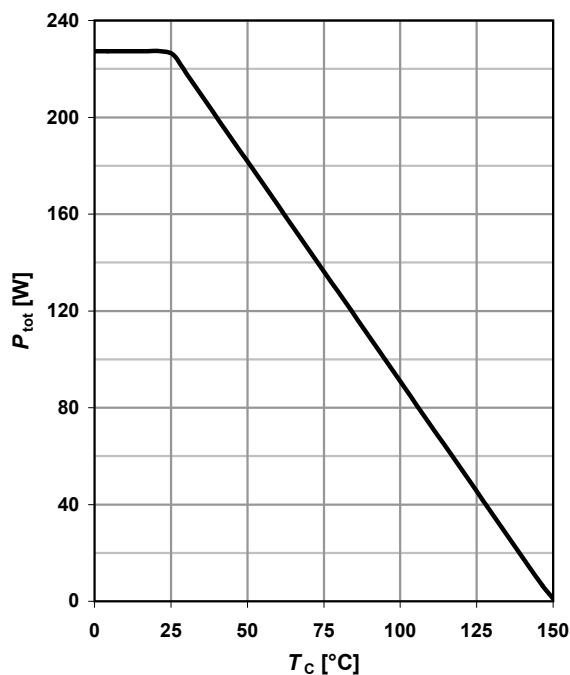
⁴⁾ Device on 40mm*40mm*1.5 epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air

⁵⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

⁶⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

1 Power dissipation

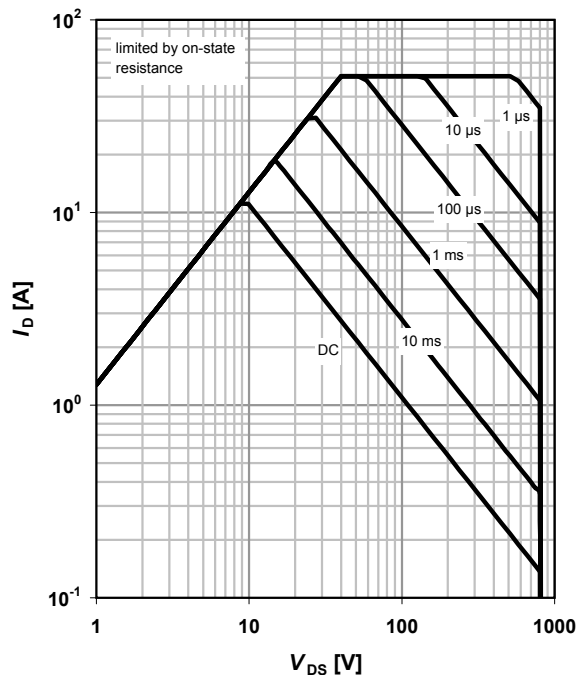
$$P_{\text{tot}} = f(T_C)$$



2 Safe operating area

$$I_D = f(V_{DS}; T_C = 25^\circ\text{C}; D = 0)$$

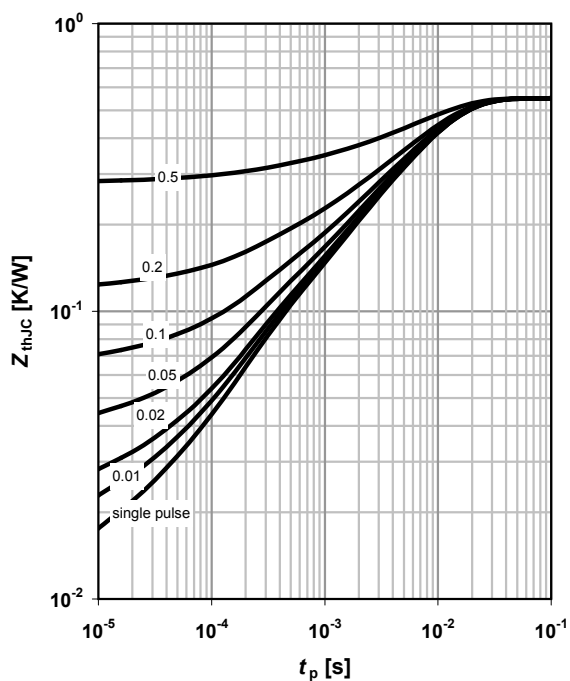
parameter: t_p



3 Max. transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

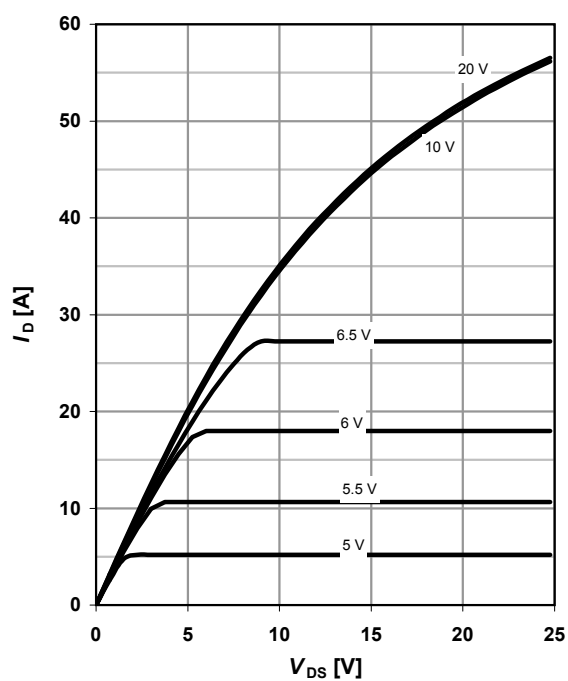
parameter: $D = t_p / T$



4 Typ. output characteristics

$$I_D = f(V_{DS}; T_J = 25^\circ\text{C})$$

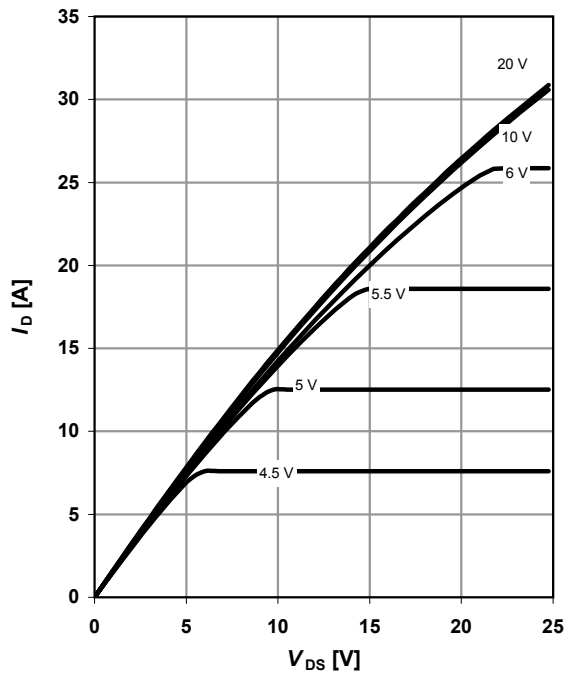
parameter: V_{GS}



5 Typ. output characteristics

$$I_D = f(V_{DS}); T_J = 150^\circ\text{C}$$

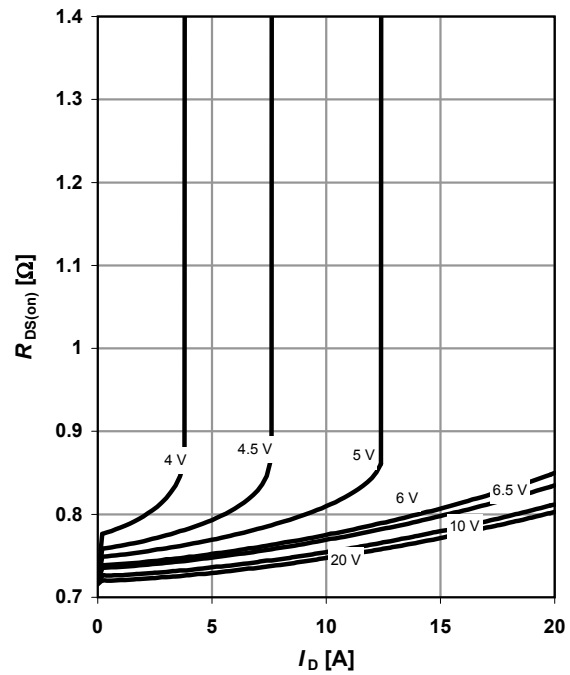
parameter: V_{GS}



6 Typ. drain-source on-state resistance

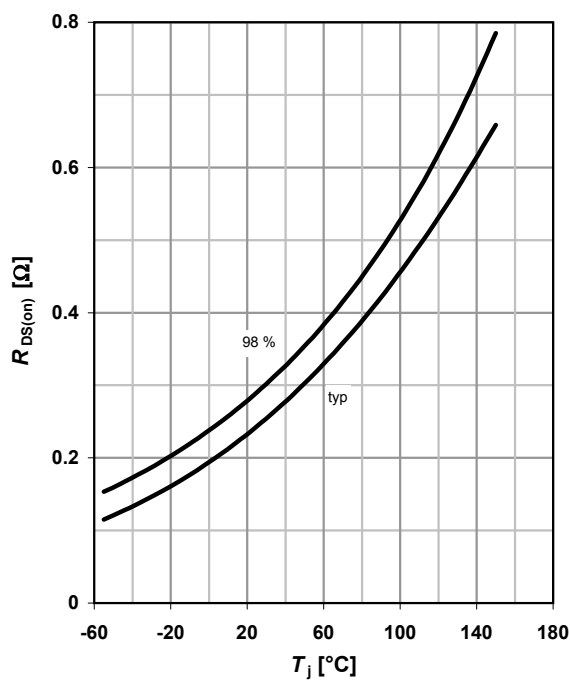
$$R_{DS(on)} = f(I_D); T_J = 150^\circ\text{C}$$

parameter: V_{GS}



7 Drain-source on-state resistance

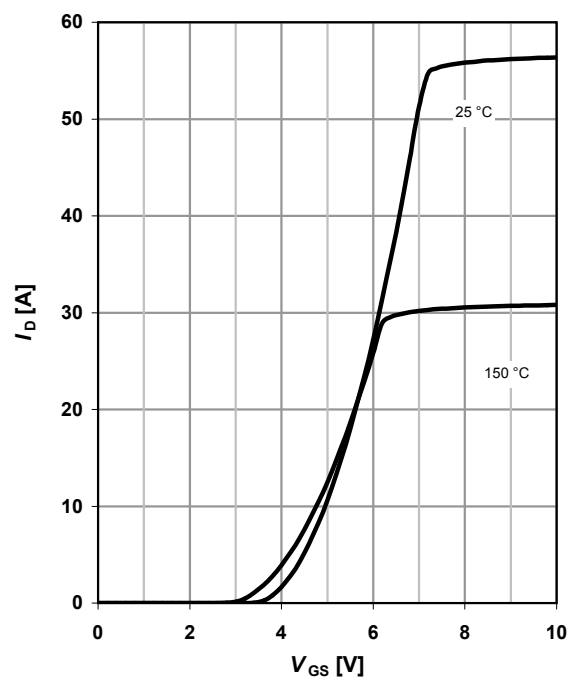
$$R_{DS(on)} = f(T_J); I_D = 11\text{ A}; V_{GS} = 10\text{ V}$$



8 Typ. transfer characteristics

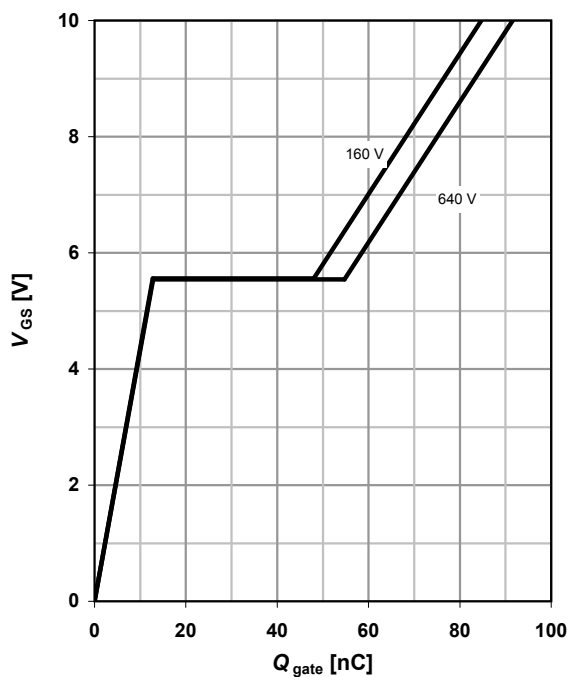
$$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|/R_{DS(on)\text{max}}$$

parameter: T_J



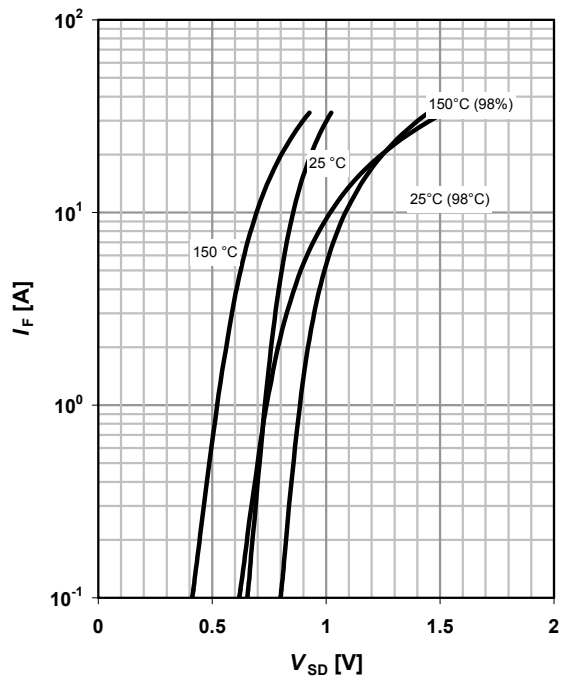
9 Typ. gate charge

 $V_{GS}=f(Q_{gate}); I_D=17\text{ A pulsed}$

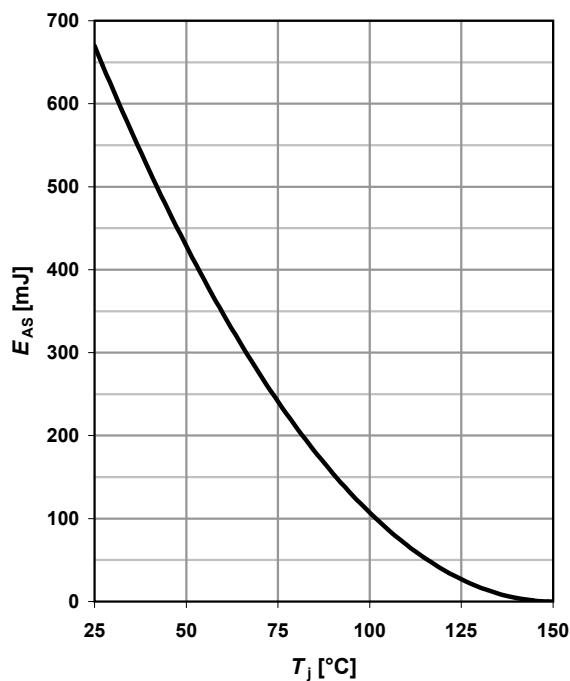
parameter: V_{DD}


10 Forward characteristics of reverse diode

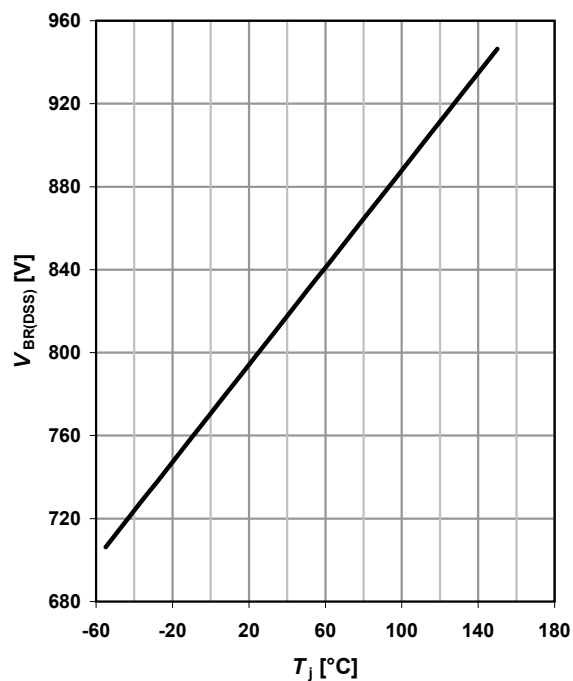
 $I_F=f(V_{SD})$

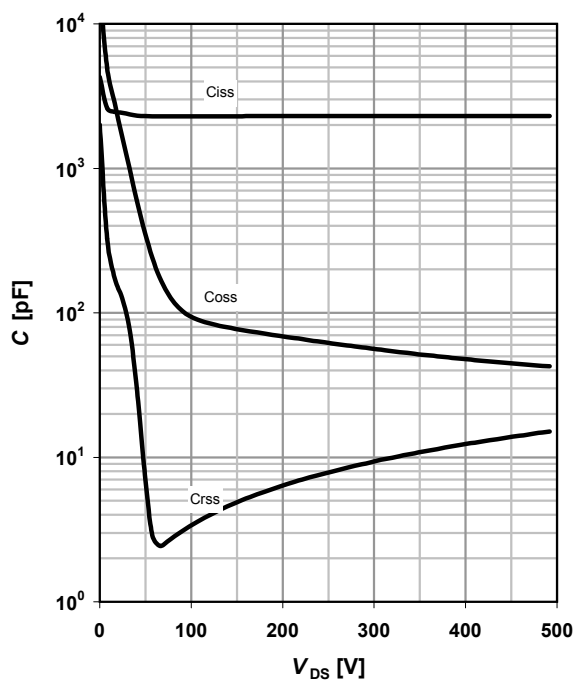
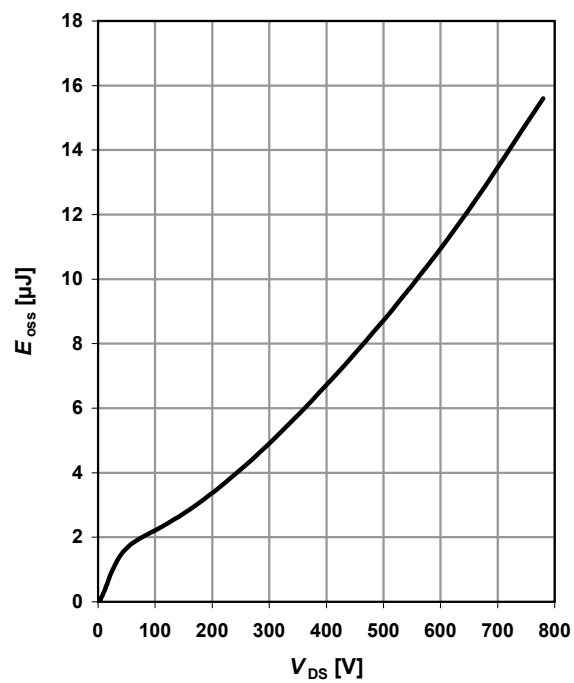
parameter: T_j


11 Avalanche energy

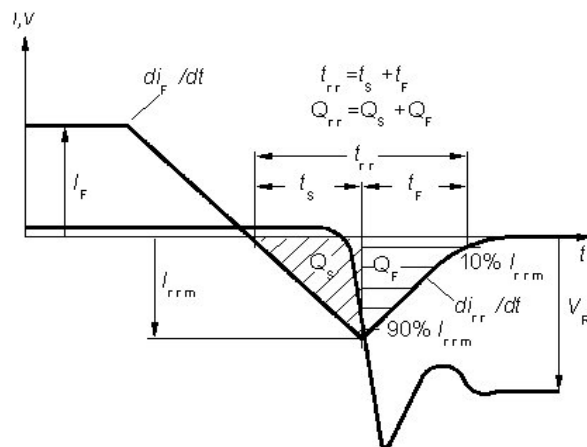
 $E_{AS}=f(T_j); I_D=3.4\text{ A}; V_{DD}=50\text{ V}$


12 Drain-source breakdown voltage

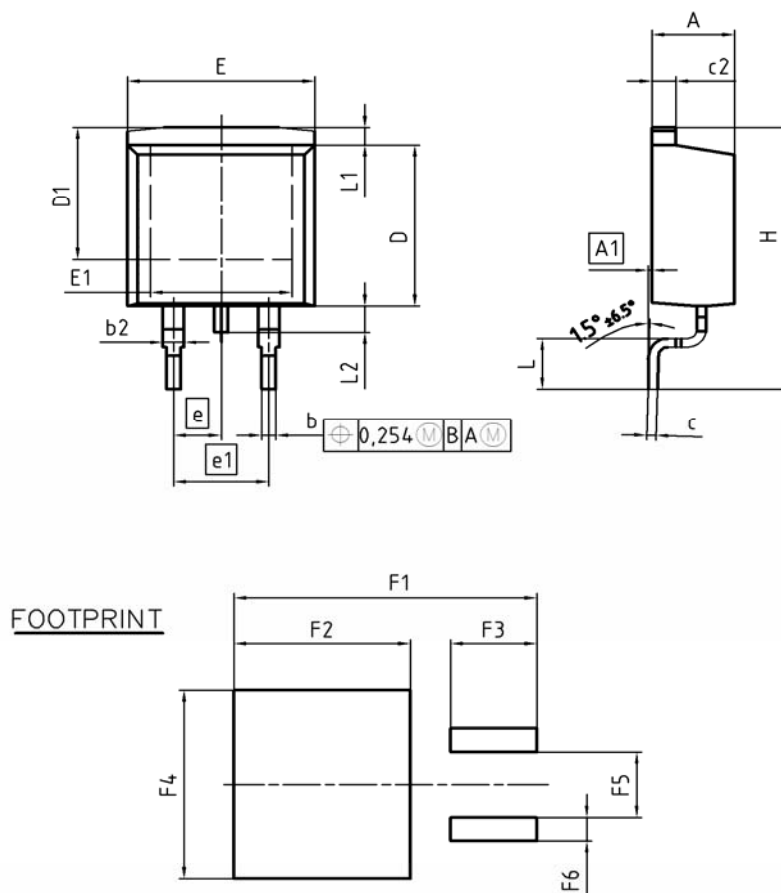
 $V_{BR(DSS)}=f(T_j); I_D=0.25\text{ mA}$


13 Typ. capacitances
 $C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

14 Typ. Coss stored energy
 $E_{oss} = f(V_{DS})$


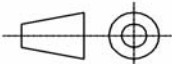
Definition of diode switching characteristics



PG-TO263: Outline



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	0.00	0.25	0.000	0.010
b	0.65	0.85	0.026	0.033
b2	0.95	1.15	0.037	0.045
c	0.33	0.65	0.013	0.026
c2	1.17	1.40	0.046	0.055
D	8.51	9.45	0.335	0.372
D1	7.10	7.90	0.280	0.311
E	9.80	10.31	0.386	0.406
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	2		2	
H	14.61	15.88	0.575	0.625
L	2.29	3.00	0.090	0.118
L1	0.70	1.60	0.028	0.063
L2	1.00	1.78	0.039	0.070
F1	16.05	16.25	0.632	0.640
F2	9.30	9.50	0.366	0.374
F3	4.50	4.70	0.177	0.185
F4	10.70	10.90	0.421	0.429
F5	3.65	3.85	0.144	0.152
F6	1.25	1.45	0.049	0.057

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